



# NX6020CAKS

60 V / 50 V, 170 mA / 160 mA N/P-channel Trench MOSFET

18 January 2018

Product data sheet

## 1. General description

Complementary N/P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Very fast switching
- ElectroStatic Discharge (ESD) protection

## 3. Applications

- Relay driver
- High-speed line driver
- Level shifter
- Power supply converter

## 4. Quick reference data

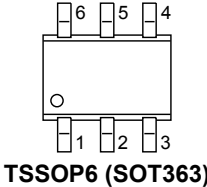
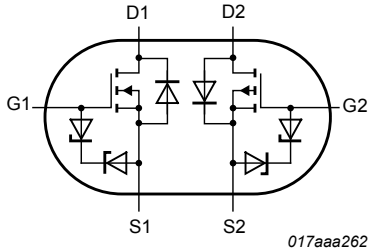
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>TR1 (N-channel)</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	60	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	170	mA
<b>TR1 (N-channel), Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 100\text{ mA}; T_j = 25\text{ °C}$	-	3	4.5	$\Omega$
<b>TR2 (P-channel)</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-50	V
$I_D$	drain current	$V_{GS} = -10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-160	mA
<b>TR2 (P-channel), Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -10\text{ V}; I_D = -100\text{ mA}; T_j = 25\text{ °C}$	-	4.5	7.5	$\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	 <p>TSSOP6 (SOT363)</p>	 <p>017aaa262</p>
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX6020CAKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

## 7. Marking

Table 4. Marking codes

Type number	Marking code[1]
NX6020CAKS	2A%

[1] % = placeholder for manufacturing site code

## 8. Limiting values

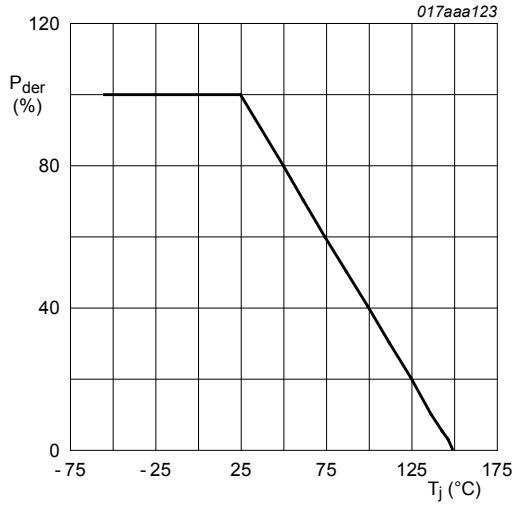
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
<b>TR1 (N-channel)</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	170	mA
		$V_{GS} = 10\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	100	mA
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ °C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	680	mA
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	220	mW
			[1]	-	255	mW
		$T_{sp} = 25\text{ °C}$		-	1.06	W
<b>TR2 (P-channel)</b>						
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$		-	-50	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	$V_{GS} = -10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	-160	mA
		$V_{GS} = -10\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	-100	mA
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ °C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	-640	mA
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	280	mW
			[1]	-	320	mW
		$T_{sp} = 25\text{ °C}$		-	990	mW
<b>Per device</b>						
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	330	mW
$T_j$	junction temperature			-55	150	°C
$T_{amb}$	ambient temperature			-55	150	°C
$T_{stg}$	storage temperature			-65	150	°C
<b>TR1 (N-channel), Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	170	mA
<b>TR2 (P-channel), Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	-160	mA

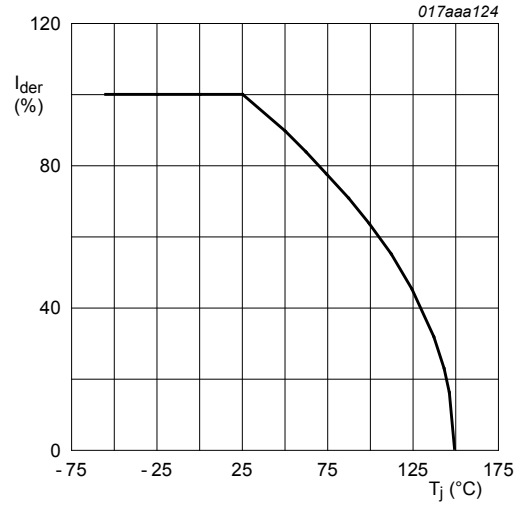
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.



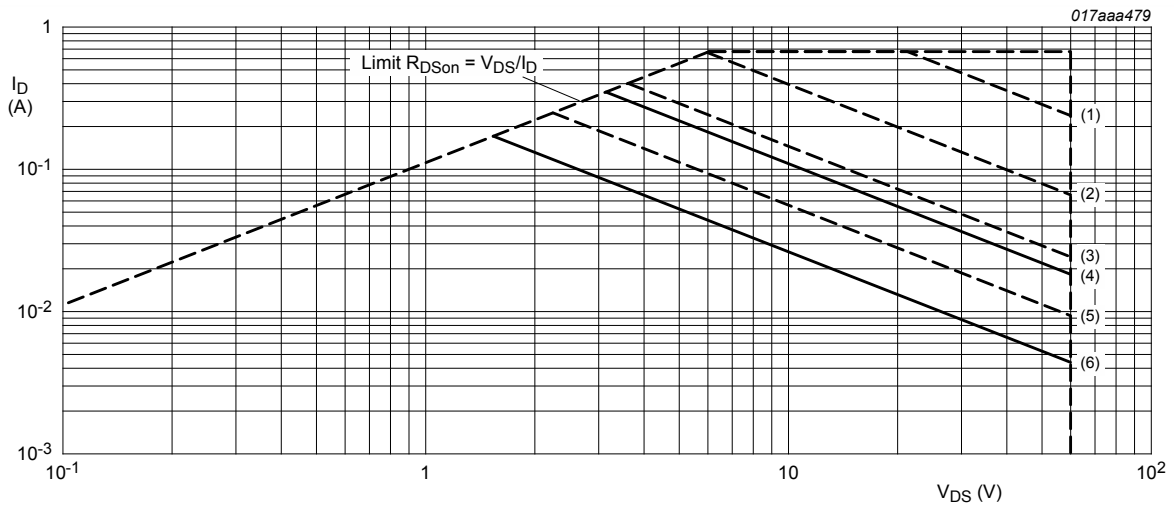
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100 \%$$

Fig. 1. Normalized total power dissipation as a function of junction temperature



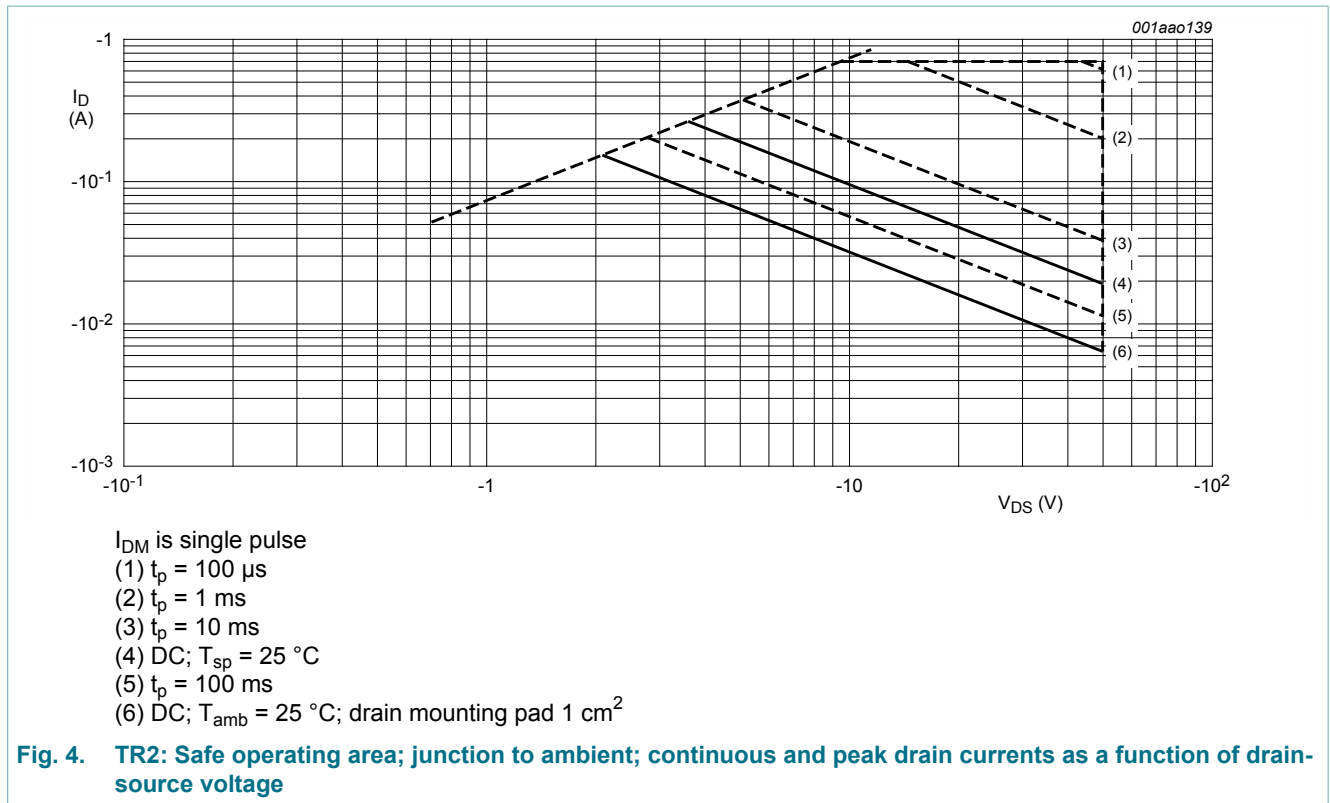
$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

Fig. 2. Normalized continuous drain current as a function of junction temperature



- $I_{DM}$  = single pulse
- (1)  $t_p = 100 \mu s$
  - (2)  $t_p = 1 ms$
  - (3)  $t_p = 10 ms$
  - (4) DC;  $T_{sp} = 25^\circ C$
  - (5)  $t_p = 100 ms$
  - (6) DC;  $T_{amb} = 25^\circ C$ ; drain mounting pad  $1 cm^2$

Fig. 3. TR1: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage



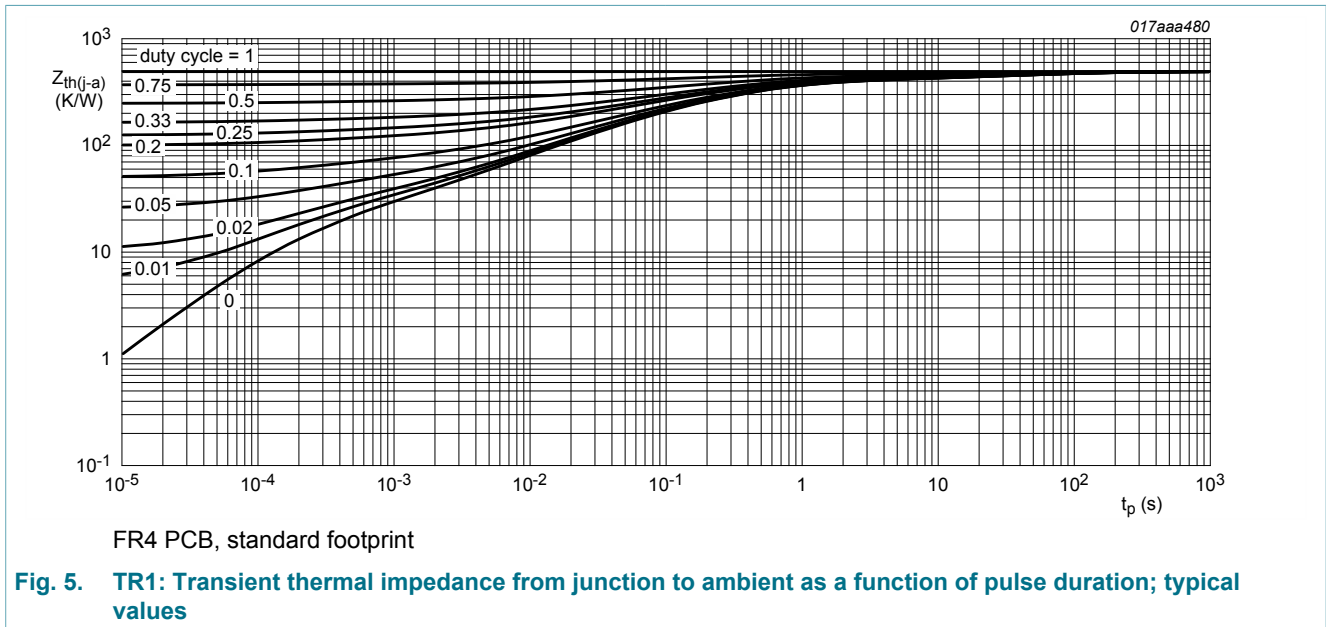
## 9. Thermal characteristics

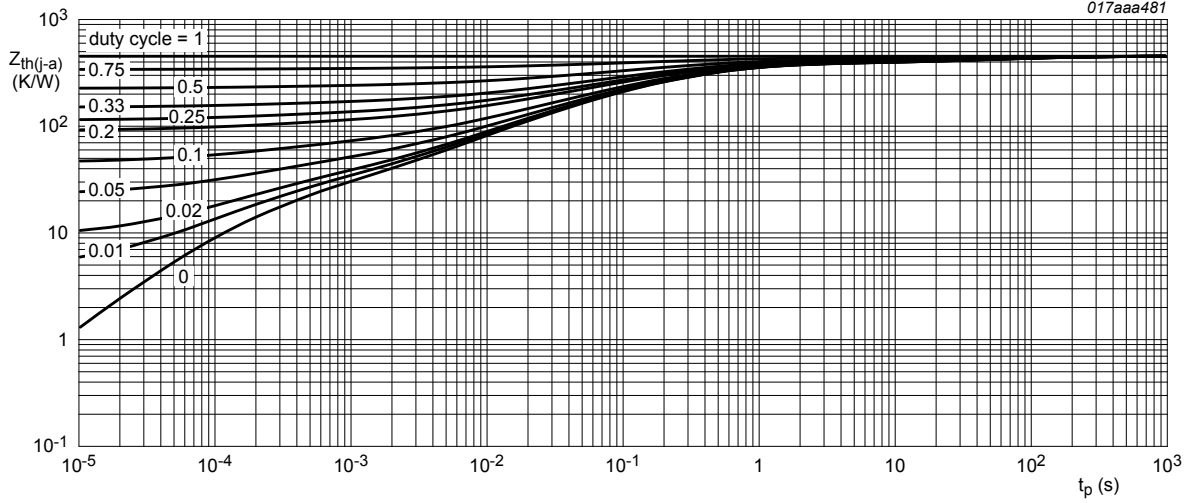
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>TR1 (N-channel)</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	500	560	K/W
			[2]	-	450	480	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	115	K/W
<b>TR2 (P-channel)</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	390	445	K/W
			[2]	-	340	390	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	130	K/W
<b>Per device</b>							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	300	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

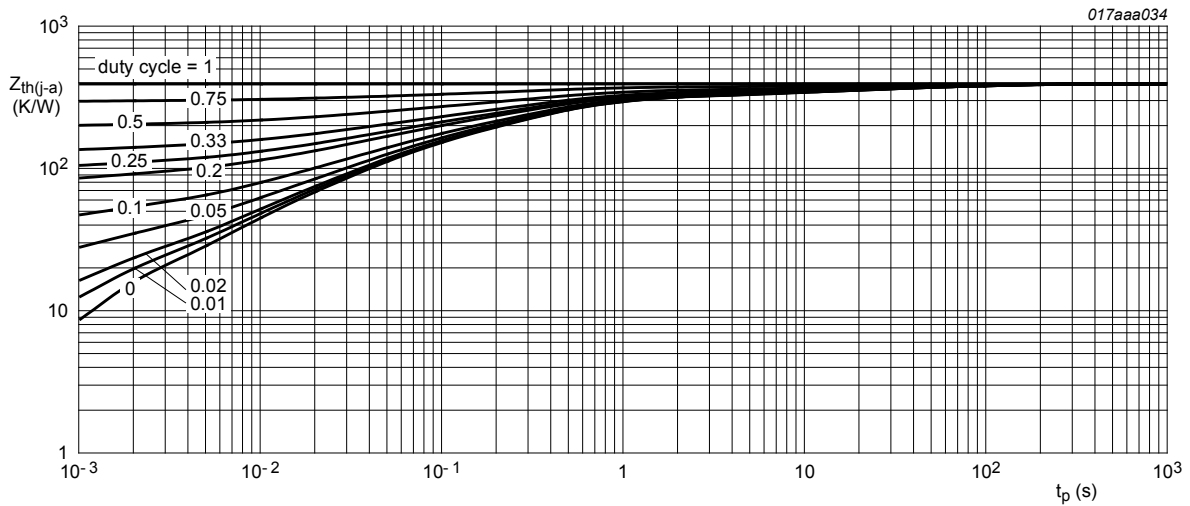
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.





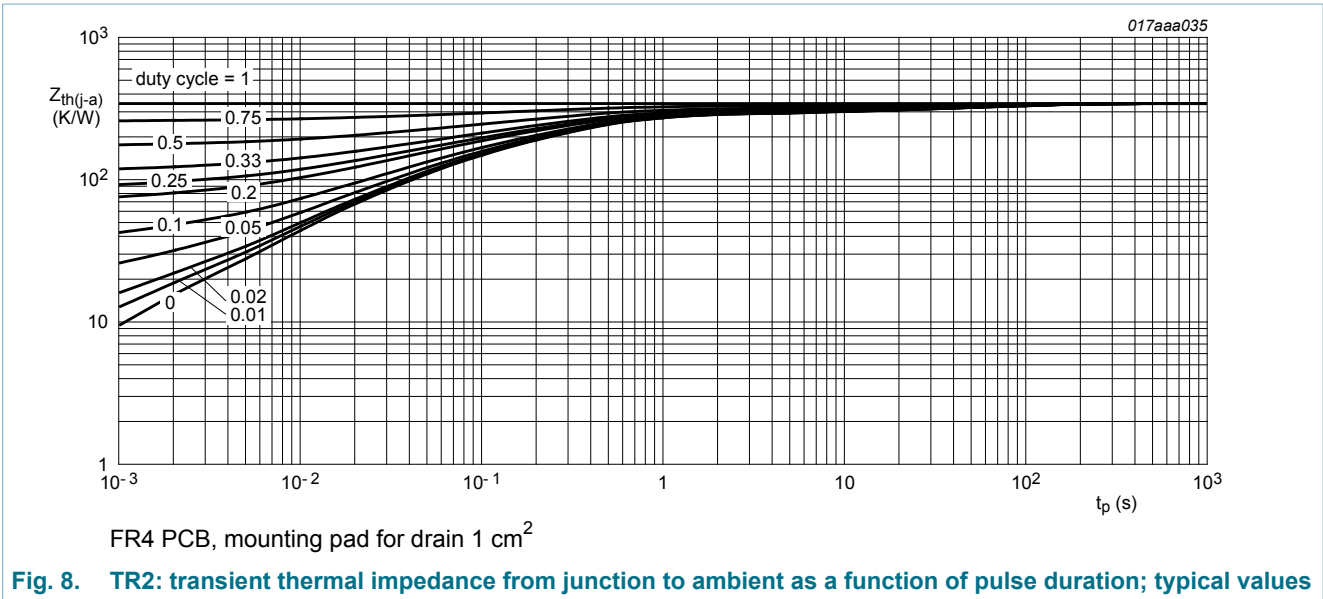
FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

**Fig. 6. TR1: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**



FR4 PCB, standard footprint

**Fig. 7. TR2: transient thermal impedance from junction to ambient as a function of pulse duration; typical values**



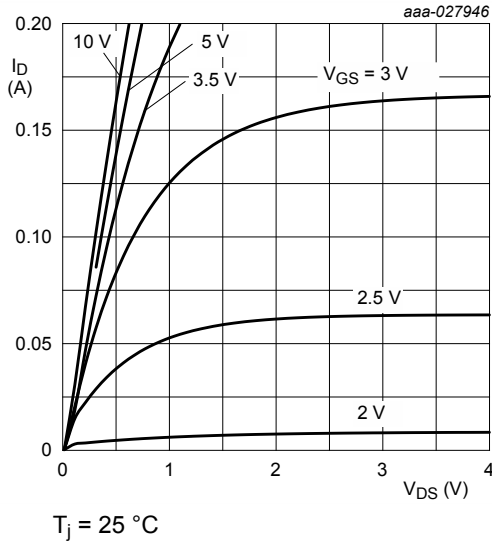


## 10. Characteristics

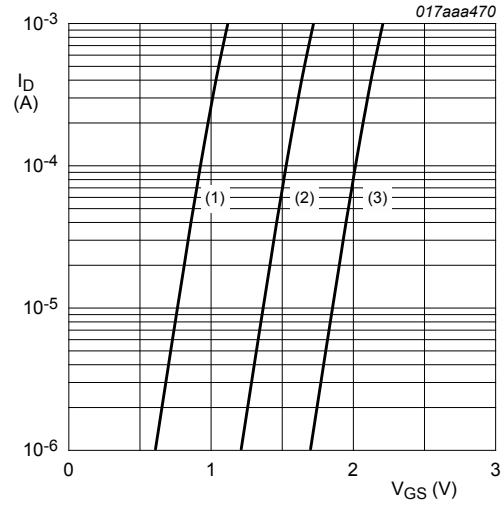
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>TR1 (N-channel), Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A$ ; $V_{DS}=V_{GS}$ ; $T_j = 25 \text{ }^\circ C$	1.1	1.6	2.1	V
$I_{DSS}$	drain leakage current	$V_{DS} = 60 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{DS} = 60 V$ ; $V_{GS} = 0 V$ ; $T_j = 150 \text{ }^\circ C$	-	-	10	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	2	$\mu A$
		$V_{GS} = -20 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	2	$\mu A$
		$V_{GS} = 10 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	0.5	$\mu A$
		$V_{GS} = -10 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	0.5	$\mu A$
		$V_{GS} = 5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 V$ ; $I_D = 100 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	3	4.5	$\Omega$
		$V_{GS} = 10 V$ ; $I_D = 100 \text{ mA}$ ; $T_j = 150 \text{ }^\circ C$	-	6.2	9.2	$\Omega$
		$V_{GS} = 5 V$ ; $I_D = 100 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	3.7	5.2	$\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10 V$ ; $I_D = 200 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	230	-	mS
<b>TR2 (P-channel), Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-50	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A$ ; $V_{DS}=V_{GS}$ ; $T_j = 25 \text{ }^\circ C$	-1.1	-1.6	-2.1	V
$I_{DSS}$	drain leakage current	$V_{DS} = -50 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
		$V_{DS} = -50 V$ ; $V_{GS} = 0 V$ ; $T_j = 150 \text{ }^\circ C$	-	-	-2	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = -20 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
		$V_{GS} = 20 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = -10 V$ ; $I_D = -100 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	4.5	7.5	$\Omega$
		$V_{GS} = -10 V$ ; $I_D = -100 \text{ mA}$ ; $T_j = 150 \text{ }^\circ C$	-	8	13.5	$\Omega$
		$V_{GS} = -5 V$ ; $I_D = -100 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	5.7	8.5	$\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = -10 V$ ; $I_D = -100 \text{ mA}$ ; $T_j = 25 \text{ }^\circ C$	-	150	-	mS
<b>TR1 (N-channel), Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 30 V$ ; $I_D = 200 \text{ mA}$ ; $V_{GS} = 4.5 V$ ; $T_j = 25 \text{ }^\circ C$	-	0.33	0.43	nC
$Q_{GS}$	gate-source charge		-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.09	-	nC

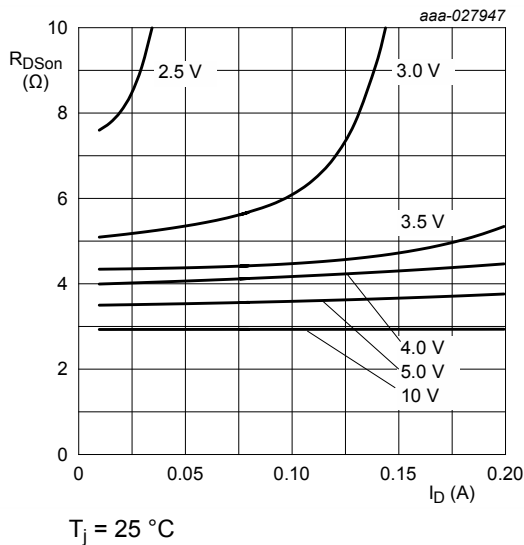
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_{iss}$	input capacitance	$V_{DS} = 10\text{ V}; f = 1\text{ MHz}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	11	17	pF
$C_{oss}$	output capacitance		-	3.4	-	pF
$C_{rss}$	reverse transfer capacitance		-	1.4	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 40\text{ V}; R_L = 250\text{ }\Omega; V_{GS} = 10\text{ V}; R_{G(ext)} = 6\text{ }\Omega; T_j = 25\text{ }^\circ\text{C}$	-	6	12	ns
$t_r$	rise time		-	7	-	ns
$t_{d(off)}$	turn-off delay time		-	20	40	ns
$t_f$	fall time		-	14	-	ns
<b>TR2 (P-channel), Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -25\text{ V}; I_D = -200\text{ mA}; V_{GS} = -5\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	0.26	0.35	nC
$Q_{GS}$	gate-source charge		-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.09	-	nC
$C_{iss}$	input capacitance	$V_{DS} = -25\text{ V}; f = 1\text{ MHz}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	24	36	pF
$C_{oss}$	output capacitance		-	4.5	-	pF
$C_{rss}$	reverse transfer capacitance		-	1.3	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -30\text{ V}; R_L = 250\text{ }\Omega; V_{GS} = -10\text{ V}; R_{G(ext)} = 6\text{ }\Omega; T_j = 25\text{ }^\circ\text{C}$	-	13	26	ns
$t_r$	rise time		-	11	-	ns
$t_{d(off)}$	turn-off delay time		-	48	96	ns
$t_f$	fall time		-	25	-	ns
<b>TR1 (N-channel), Source-drain diode characteristics</b>						
$V_{SD}$	source-drain voltage	$I_S = 115\text{ mA}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	0.47	0.7	1.2	V
<b>TR2 (P-channel), Source-drain diode characteristics</b>						
$V_{SD}$	source-drain voltage	$I_S = -115\text{ mA}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-0.48	-0.85	-1.2	V



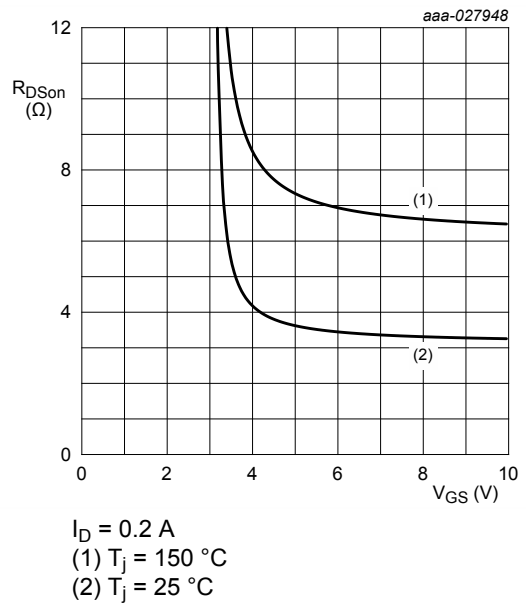
**Fig. 9. TR1: Output characteristics: drain current as a function of drain-source voltage; typical values**



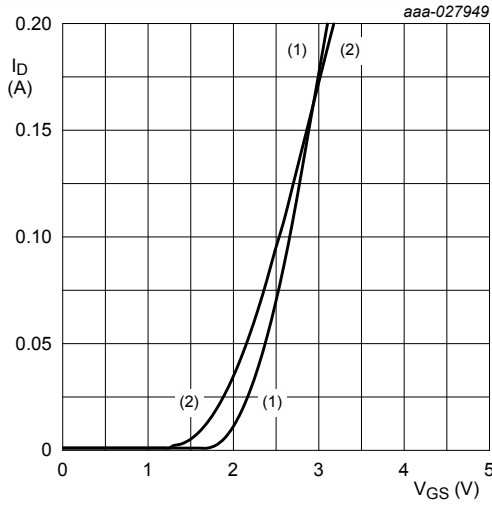
**Fig. 10. TR1: Sub-threshold drain current as a function of gate-source voltage**  
 (1) minimum values  
 (2) typical values  
 (3) maximum values



**Fig. 11. TR1: Drain-source on-state resistance as a function of drain current; typical values**

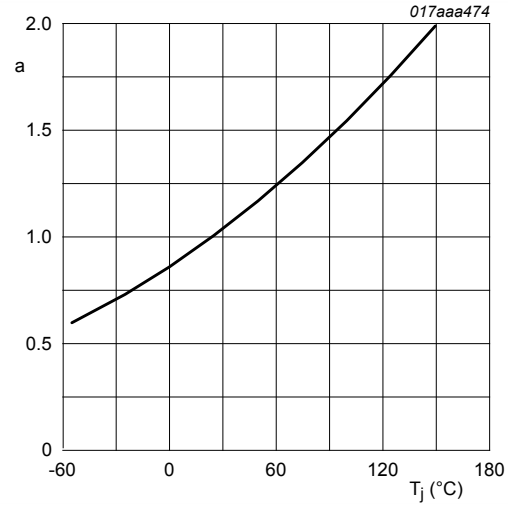


**Fig. 12. TR1: Drain-source on-state resistance as a function of gate-source voltage; typical values**



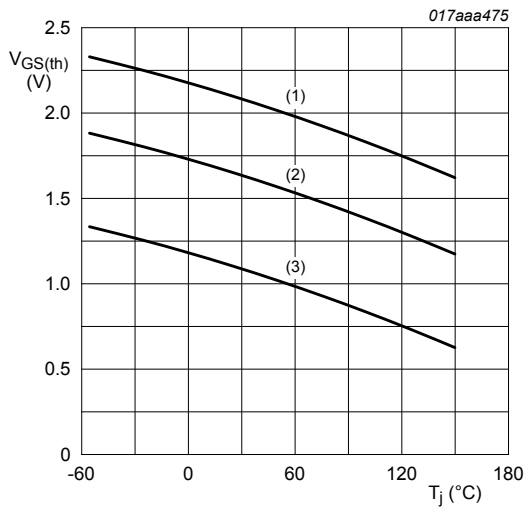
$V_{DS} > I_D \times R_{DSon}$   
 (1)  $T_j = 25\text{ °C}$   
 (2)  $T_j = 150\text{ °C}$

**Fig. 13. TR1: Transfer characteristics: drain current as a function of gate-source voltage; typical values**



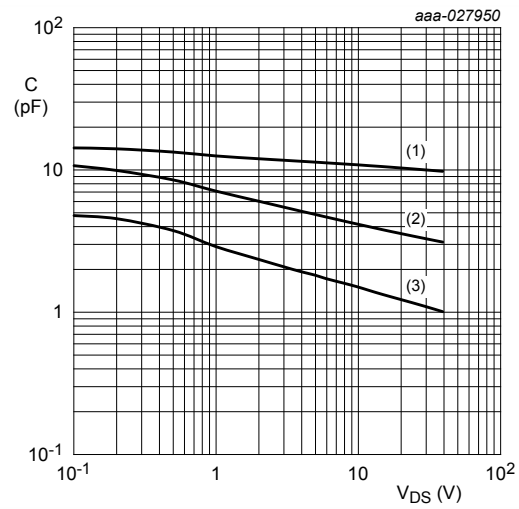
$$a = \frac{R_{DSon}}{R_{DSon}(25\text{ °C})}$$

**Fig. 14. TR1: Normalized drain-source on-state resistance as a function of junction temperature; typical values**



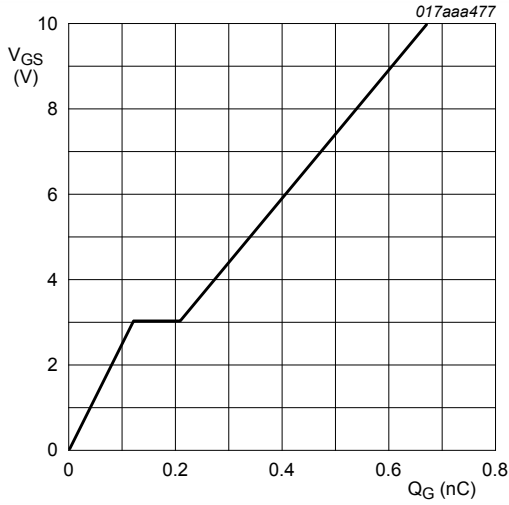
$I_D = 0.25\text{ mA}; V_{DS} = V_{GS}$   
 (1) maximum values  
 (2) typical values  
 (3) minimum values

**Fig. 15. TR1: Gate-source threshold voltage as a function of junction temperature**



$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$   
 (1)  $C_{iss}$   
 (2)  $C_{oss}$   
 (3)  $C_{rss}$

**Fig. 16. TR1: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



$I_D = 0.2 \text{ A}; V_{DS} = 30 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 17. TR1: Gate-source voltage as a function of gate charge; typical values

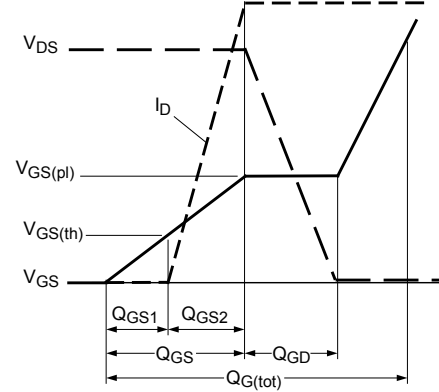
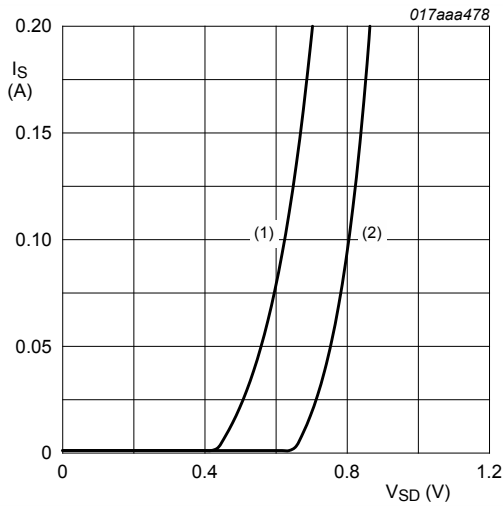
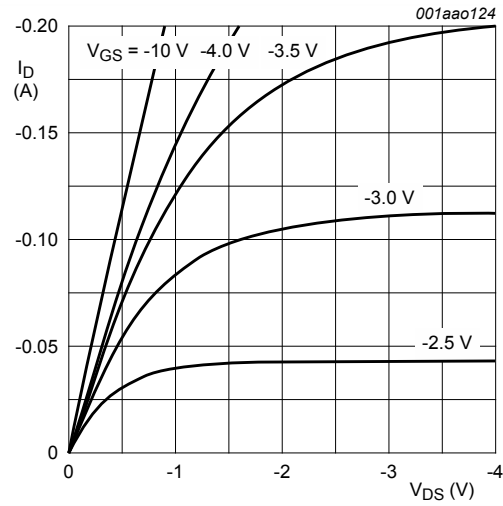


Fig. 18. TR1: Gate charge waveform definitions



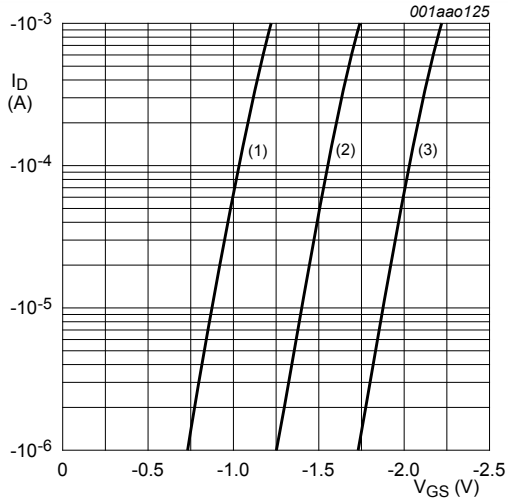
$V_{GS} = 0 \text{ V}$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$   
 (2)  $T_j = 25 \text{ }^\circ\text{C}$

Fig. 19. TR1: Source current as a function of source-drain voltage; typical values



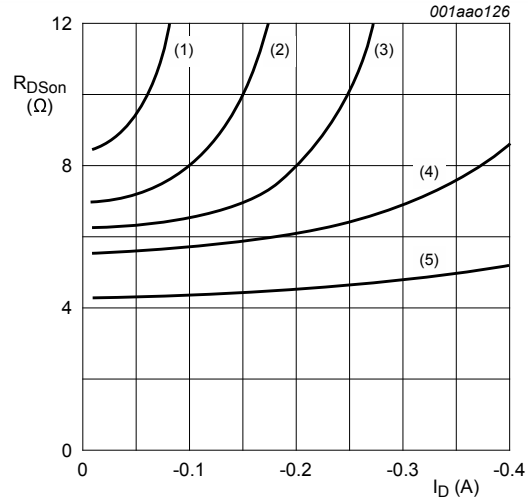
$T_j = 25 \text{ }^\circ\text{C}$

Fig. 20. TR2: Output characteristics: drain current as a function of drain-source voltage; typical values



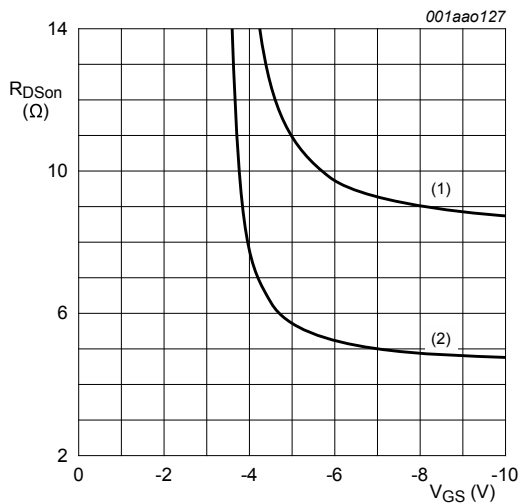
$T_j = 25\text{ }^\circ\text{C}$ ;  $V_{DS} = -5\text{ V}$   
 (1) minimum values  
 (2) typical values  
 (3) maximum values

**Fig. 21. TR2: Sub-threshold drain current as a function of gate-source voltage**



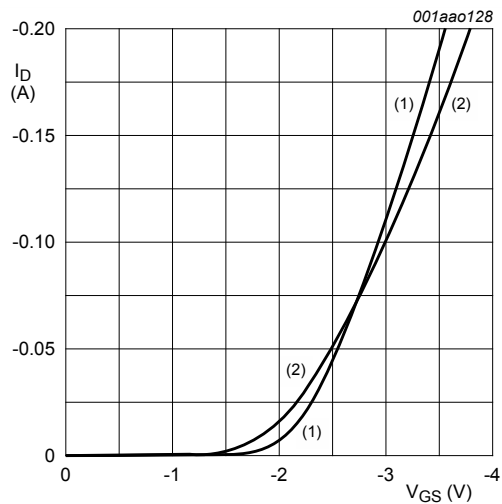
$T_j = 25\text{ }^\circ\text{C}$   
 (1)  $V_{GS} = -3.0\text{ V}$   
 (2)  $V_{GS} = -3.5\text{ V}$   
 (3)  $V_{GS} = -4.0\text{ V}$   
 (4)  $V_{GS} = -5.0\text{ V}$   
 (5)  $V_{GS} = -10.0\text{ V}$

**Fig. 22. TR2: Drain-source on-state resistance as a function of drain current; typical values**



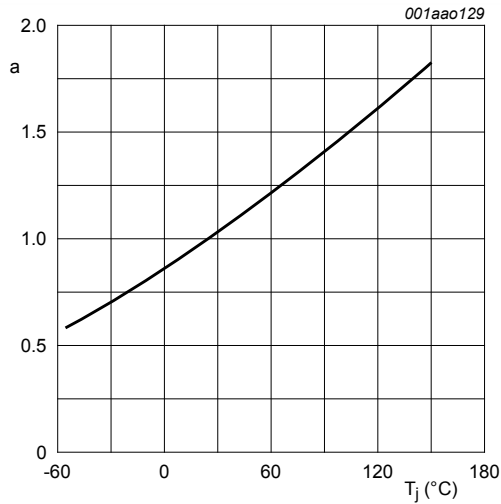
$I_D = -200\text{ mA}$   
 (1)  $T_j = 150\text{ }^\circ\text{C}$   
 (2)  $T_j = 25\text{ }^\circ\text{C}$

**Fig. 23. TR2: Drain-source on-state resistance as a function of gate-source voltage; typical values**



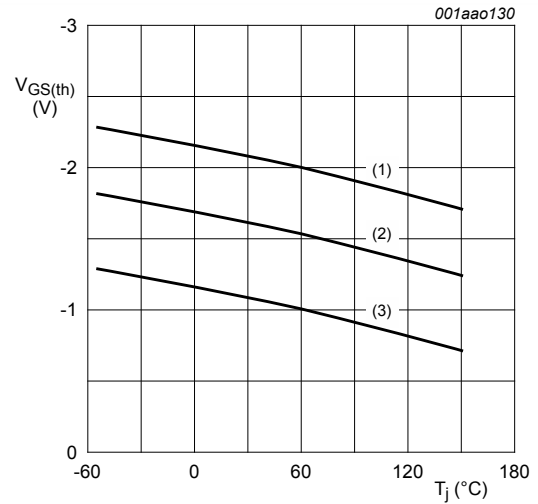
$V_{DS} > I_D \times R_{DSon}$   
 (1)  $T_j = 25\text{ }^\circ\text{C}$   
 (2)  $T_j = 150\text{ }^\circ\text{C}$

**Fig. 24. TR2: Transfer characteristics: drain current as a function of gate-source voltage; typical values**



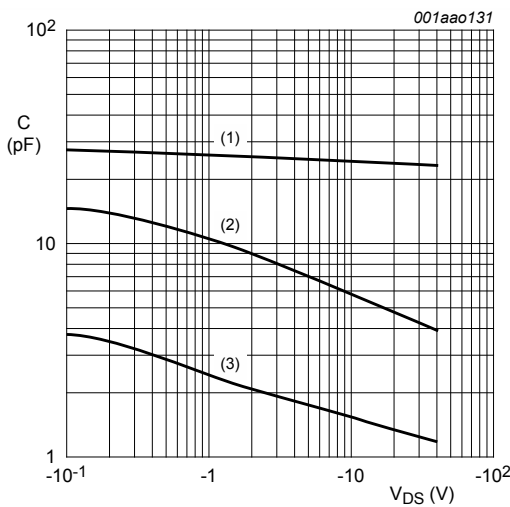
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

**Fig. 25. TR2: Normalized drain-source on-state resistance as a function of junction temperature; typical values**



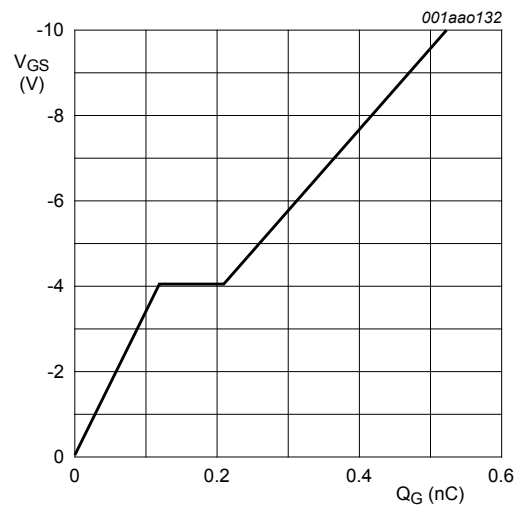
$I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$   
 (1) maximum values  
 (2) typical values  
 (3) minimum values

**Fig. 26. TR2: Gate-source threshold voltage as a function of junction temperature**



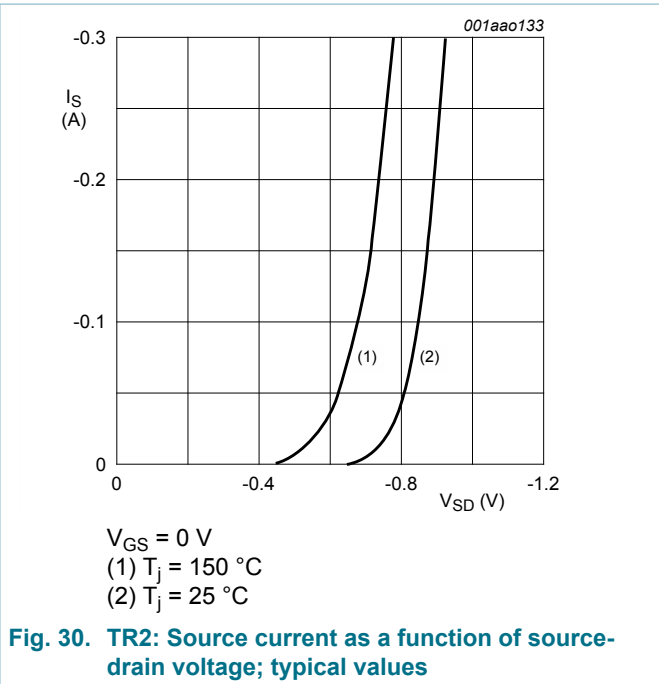
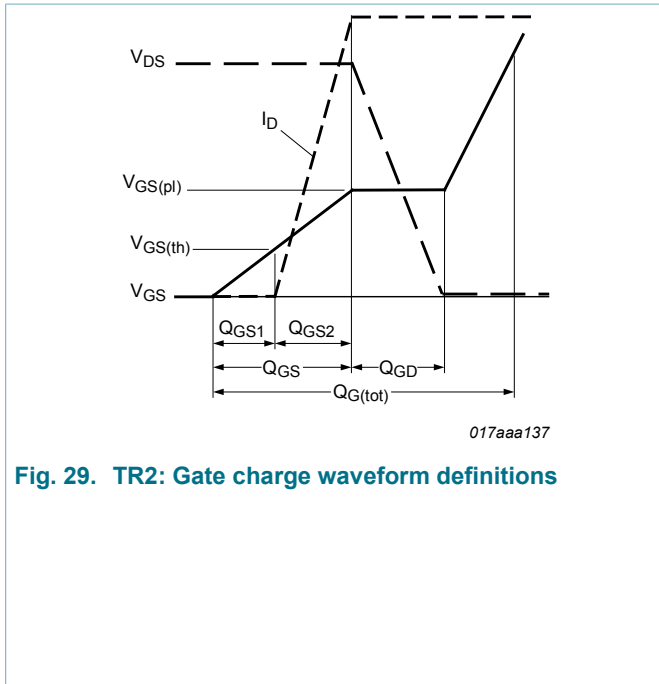
$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$   
 (1)  $C_{iss}$   
 (2)  $C_{oss}$   
 (3)  $C_{rss}$

**Fig. 27. TR2: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

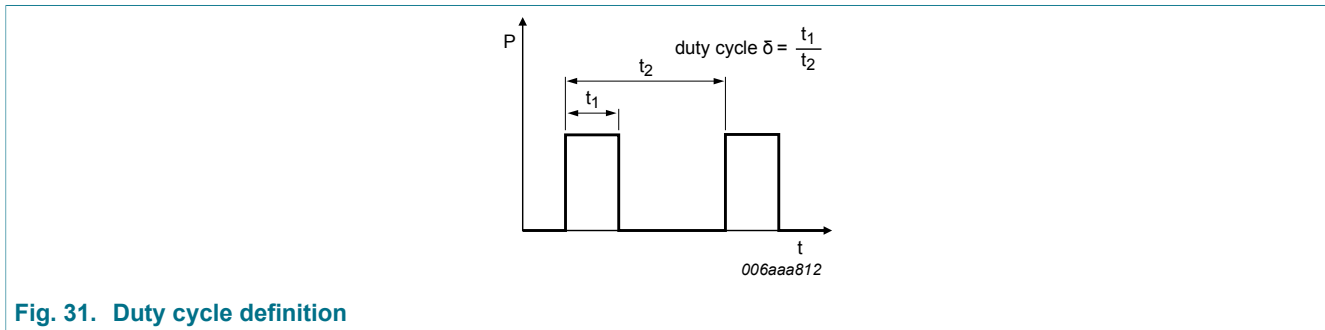


$I_D = -200 \text{ mA}; V_{DS} = -25 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig. 28. TR2: Gate-source voltage as a function of gate charge; typical values**



## 11. Test information





## 12. Package outline

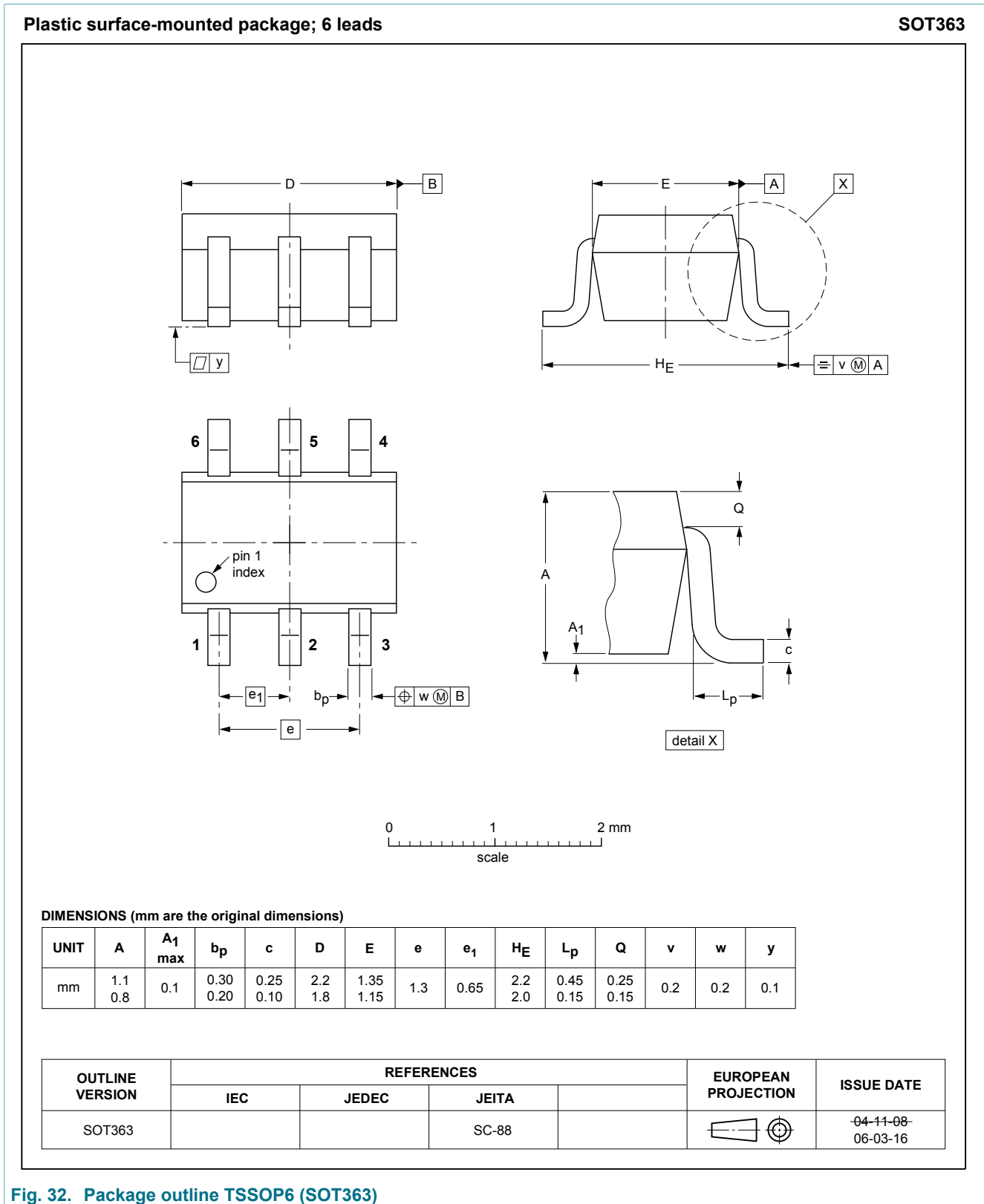


Fig. 32. Package outline TSSOP6 (SOT363)

### 13. Soldering

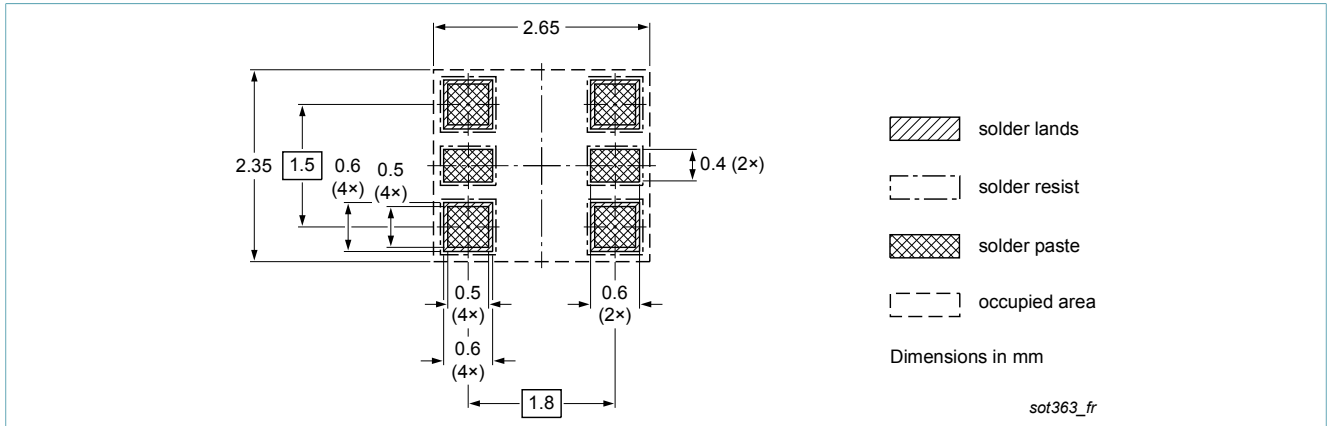


Fig. 33. Reflow soldering footprint for TSSOP6 (SOT363)

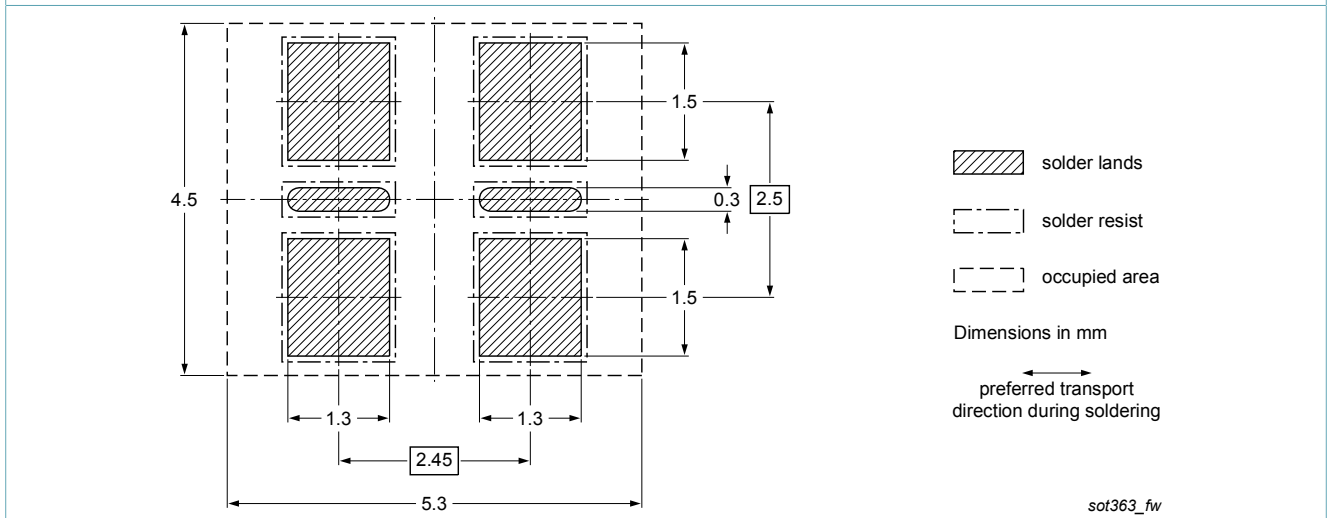


Fig. 34. Wave soldering footprint for TSSOP6 (SOT363)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX6020CAKS v.2	20180118	Product data sheet	-	NX6020CAKS v.1
Modifications:	<ul style="list-style-type: none"><li>• Data sheet status changed to Product.</li><li>• Section: Limiting values, ESD maximum rating removed.</li></ul>			
NX6020CAKS v.1	20171220	Preliminary data sheet	-	-

## 15. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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